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ICE4N73 N-Channel Enhancement Mode MOSFET

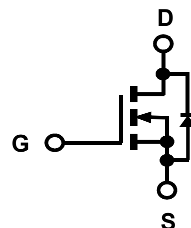
RoHS compliant 2011/65/EU

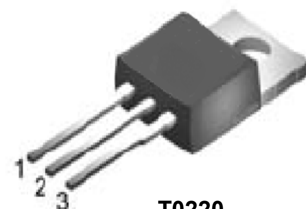
HALOGEN **FREE**

Product Summary			
I_D	T_C=25°C	4A	Max
$V_{(BR)DSS}$	I_D=250uA	730V	Min
$r_{DS(on)}$	V_{GS}=10V	0.77Ω	Typ
Q_g	V_{DS}=480V	22nC	Typ

Features

- Low $r_{DS(on)}$
- Ultra Low Gate Charge
- High d*v*/d*t* capability
- High Unclamped Inductive Switching (UIS) capability
- High peak current capability
- Increased transconductance performance
- Optimized design for high performance power systems





T0220

Standard Metal Heatsink

1=Gate, 2=Drain, 3=Source.

ICEMOS AND ITS SISTER COMPANY 3D SEMI OWN THE FUNDAMENTAL PATENTS FOR SUPERJUNCTION MOSFETS. THE MAJORITY OF THESE PATENTS HAVE 17 to 20 YEARS OF REMAINING LIFE. THIS PORTFOLIO HAS GRANTED PATENTS ISSUED IN USA, CHINA, KOREA, JAPAN, TAIWAN & EUROPE.

Maximum ratings at T_j=25°C, unless otherwise specified

Parameter	*Symbol*	*Conditions*	*Value*	*Unit*
Continuous drain current	I_D	T_c=25°C T_c=100°C	4 2.7	A
Pulsed drain current	$I_{D,\ pulse}$	T_c=25°C	12	A
Avalanche energy, single pulse	E_{AS}	I_D=2A	80	mJ
Avalanche current, repetitive	I_{AR}	limited by $T_j$max	2	A
MOSFET d*v*/d*t* ruggedness	d*v*/d*t*	V_{DS}=480V, I_D=4A, T_j=125°C	50	V/ns
Gate source voltage	V_{GS}	Static	±20	V
		AC (*f*>1Hz)	±30	
Power dissipation	P_{tot}	T_c=25°C	65	W
Operating and storage temperature	T_j, T_{stg}		-55 to +150	°C
Mounting torque		M 3 & 3.5 screws	60	Ncm

a When mounted on 1inch square 2oz copper clad FR-4

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Thermal characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Thermal resistance, junction-case	R_{thJC}		-	-	1.9	°C/W
Thermal resistance, junction-ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wave soldering only allowed at leads	T_{sold}	1.6mm (0.063in.) from case for 10 s	-	-	260	°C

Electrical characteristics at T_j=25°C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=250μA	730	773	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2.1	3.1	3.9	
Zero gate voltage drain current	I_{DSS}	V_{DS}=730V, V_{GS}=0V, T_j=25°C	-	0.04	5	μA
		V_{DS}=730V, V_{GS}=0V, T_j=150°C	-	14	-	
Gate source leakage current	I_{GSS}	V_{GS}=±20 V, V_{DS}=0V	-	-	100	nA
Drain-source on-state resistance	$r_{DS(on)}$	V_{GS}=10V, I_D=2A, T_j=25°C	-	0.77	1.2	Ω
		V_{GS}=10V, I_D=2A, T_j=150°C	-	2.3	-	
Gate resistance	R_G	f=1 MHZ, open drain	-	3.8	-	Ω

Dynamic characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=25 V, f=1 MHz	-	625	-	pF
Output capacitance	C_{oss}		-	59	-	
Reverse transfer capacitance	C_{rss}		-	1.2	-	
Transconductance	g_{fs}	V_{DS}>2*I_D*R_{DS}, I_D=2A	-	4	-	S
Turn-on delay time	$t_{d(on)}$	V_{DS}=480V, V_{GS}=10V, I_D=4A, R_G=4Ω (External)	-	22	-	ns
Rise time	t_r		-	23	-	
Turn-off delay time	$t_{d(off)}$		-	52	-	
Fall time	t_f		-	18	-	

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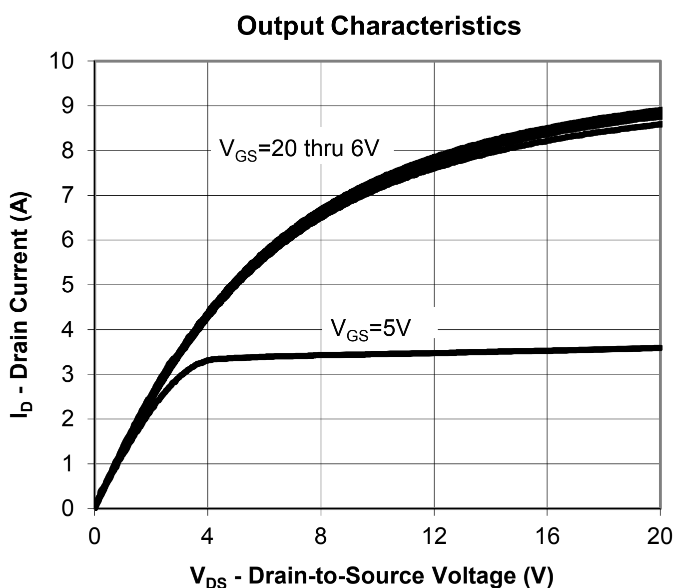
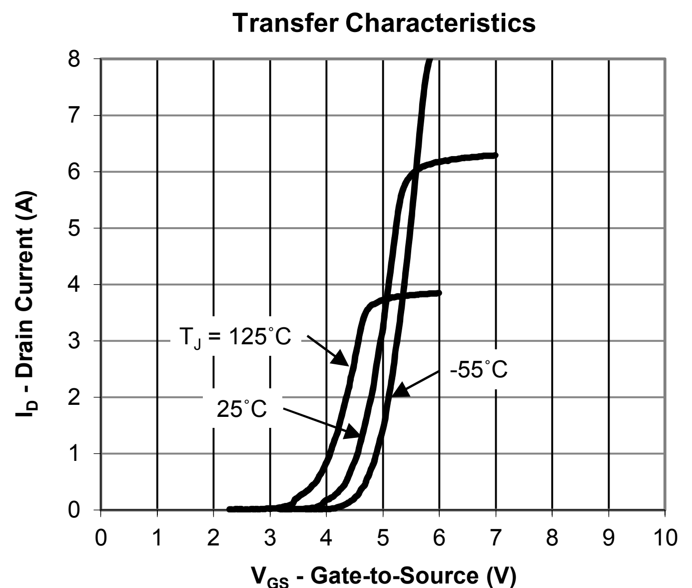
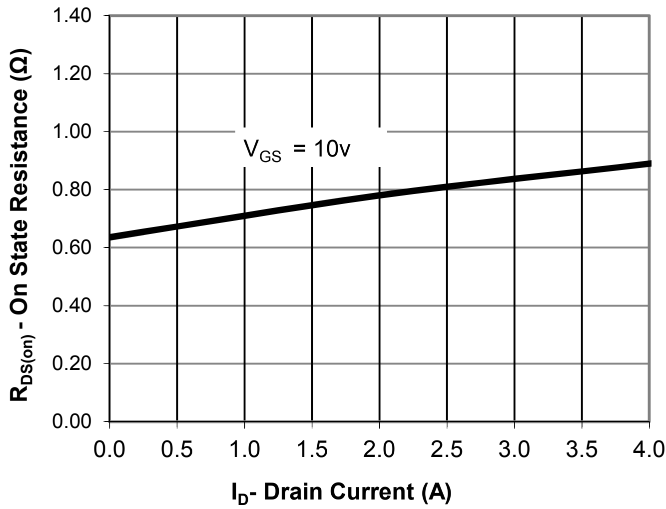
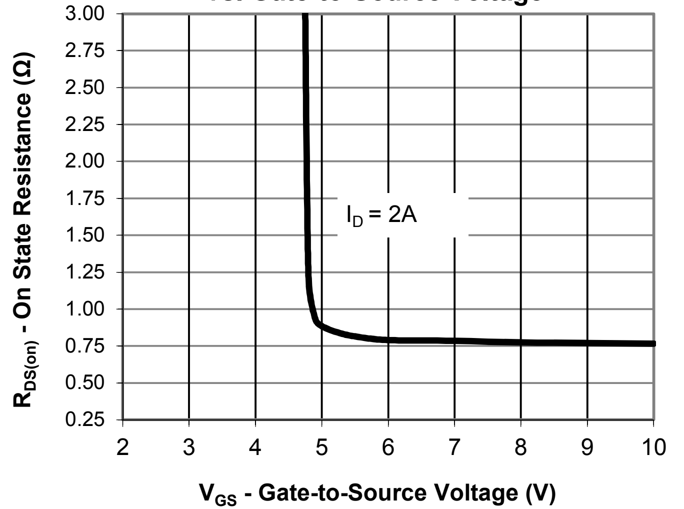
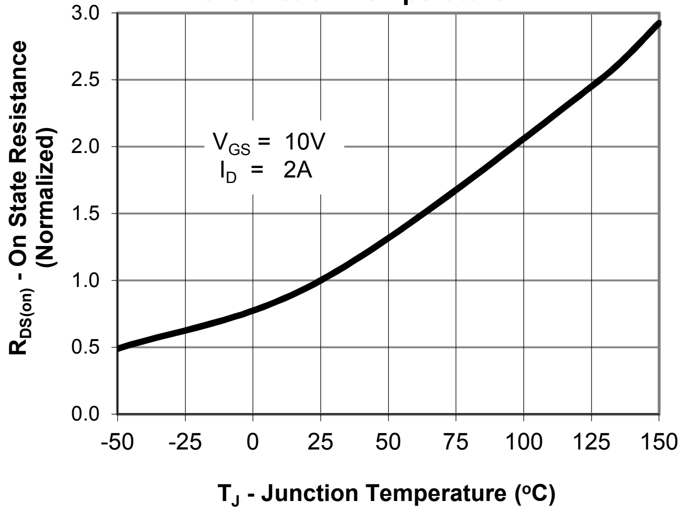
Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DS}=480 V, I_D=4A, V_{GS}=0 to 10 V	-	3.6	-	nC
Gate to drain charge	Q_{gd}		-	7.9	-	nC
Gate charge total	Q_g		-	22	-	nC
Gate plateau voltage	$V_{plateau}$		-	5.1	-	V
Reverse Diode						
Continuous forward current	I_S	V_{GS}=0V	-	-	4	A
Diode forward voltage	V_{SD}	V_{GS}=0V, I_S=I_F	-	0.8	1.2	V
Reverse recovery time	t_{rr}	V_{RR}=100V, I_S=I_F, d_{iF}/d_t=100 A/µS	-	240	-	ns
Reverse recovery charge	Q_{rr}		-	2.5	-	µC
Peak reverse recovery current	I_{rm}		-	20	-	A

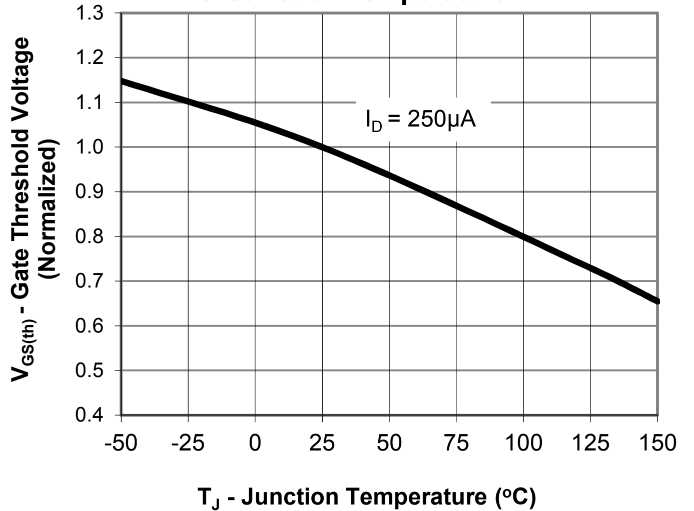


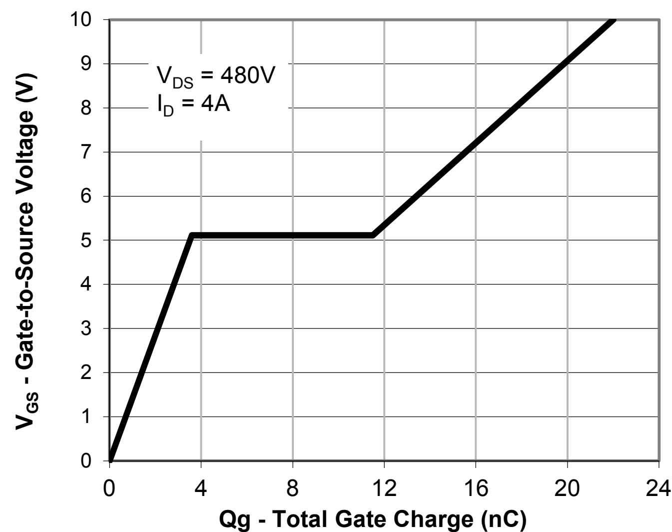


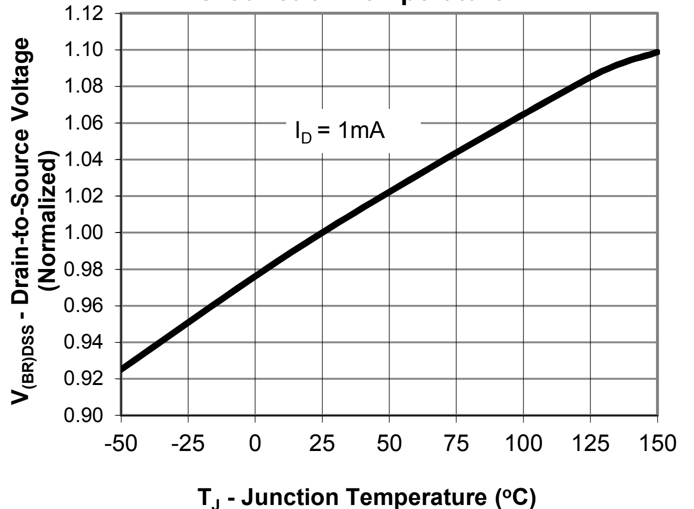

Drain-Source On-State Resistance
vs. Drain Current
$R_{DS(on)}$ - On State Resistance (Ω)
V_{GS} = 10v
1.40
1.20
1.00
0.80
0.60
0.40
0.20
0.00
0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0
I_D- Drain Current (A)


Drain-Source On-State Resistance
vs. Gate-to-Source Voltage
$R_{DS(on)}$ - On State Resistance (Ω)
I_D = 2A
3.00
2.75
2.50
2.25
2.00
1.75
1.50
1.25
1.00
0.75
0.50
0.25
2 3 4 5 6 7 8 9 10
V_{GS} - Gate-to-Source Voltage (V)

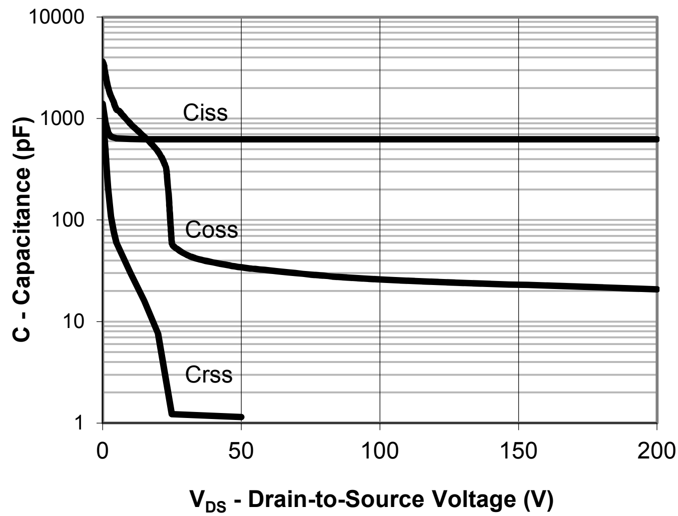

Drian-Source On State Resistance
vs. Junction Temperature
$R_{DS(on)}$ - On State Resistance
(Normalized)
V_{GS} = 10V
I_D = 2A
3.0
2.5
2.0
1.5
1.0
0.5
0.0
-50 -25 0 25 50 75 100 125 150
T_J - Junction Temperature (°C)


Gate Threshold Voltage
vs. Junction Temperature
$V_{GS(th)}$ - Gate Threshold Voltage
(Normalized)
I_D = 250μA
1.3
1.2
1.1
1.0
0.9
0.8
0.7
0.6
0.5
0.4
-50 -25 0 25 50 75 100 125 150
T_J - Junction Temperature (°C)

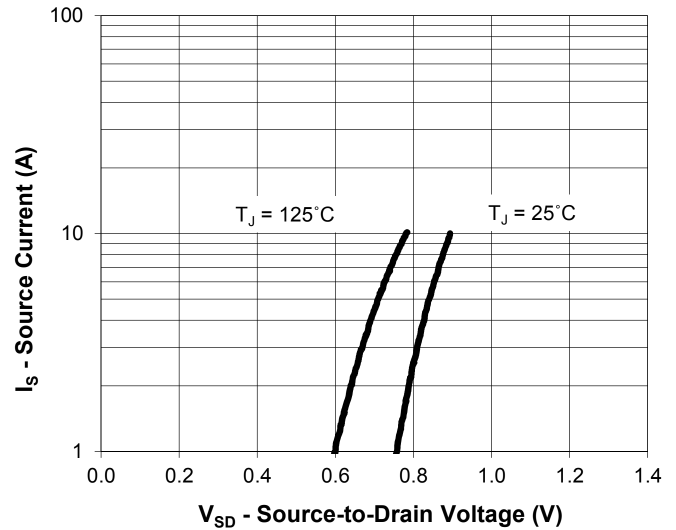

Gate Charge
V_{GS} - Gate-to-Source Voltage (V)
V_{DS} = 480V
I_D = 4A
10
9
8
7
6
5
4
3
2
1
0
0 4 8 12 16 20 24
Qg - Total Gate Charge (nC)


Drain-toSource Breakdown Voltage
vs. Junction Temperature
$V_{(BR)DSS}$ - Drain-to-Source Voltage
(Normalized)
I_D = 1mA
1.12
1.10
1.08
1.06
1.04
1.02
1.00
0.98
0.96
0.94
0.92
0.90
-50 -25 0 25 50 75 100 125 150
T_J - Junction Temperature (°C)

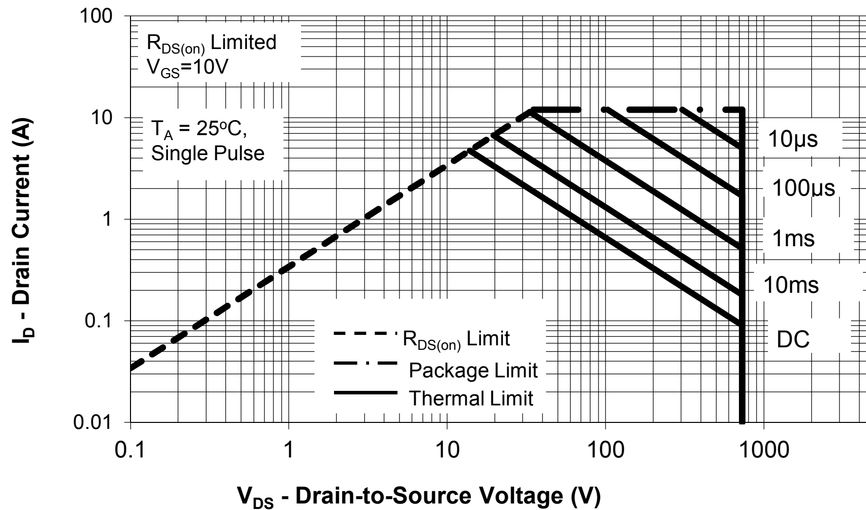
Capacitance



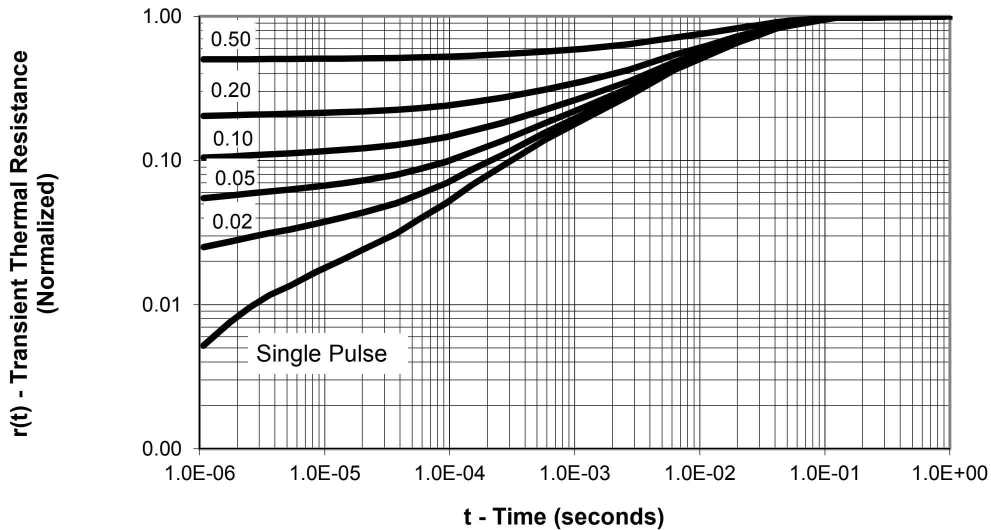
Source-Drain Diode Forward Voltage

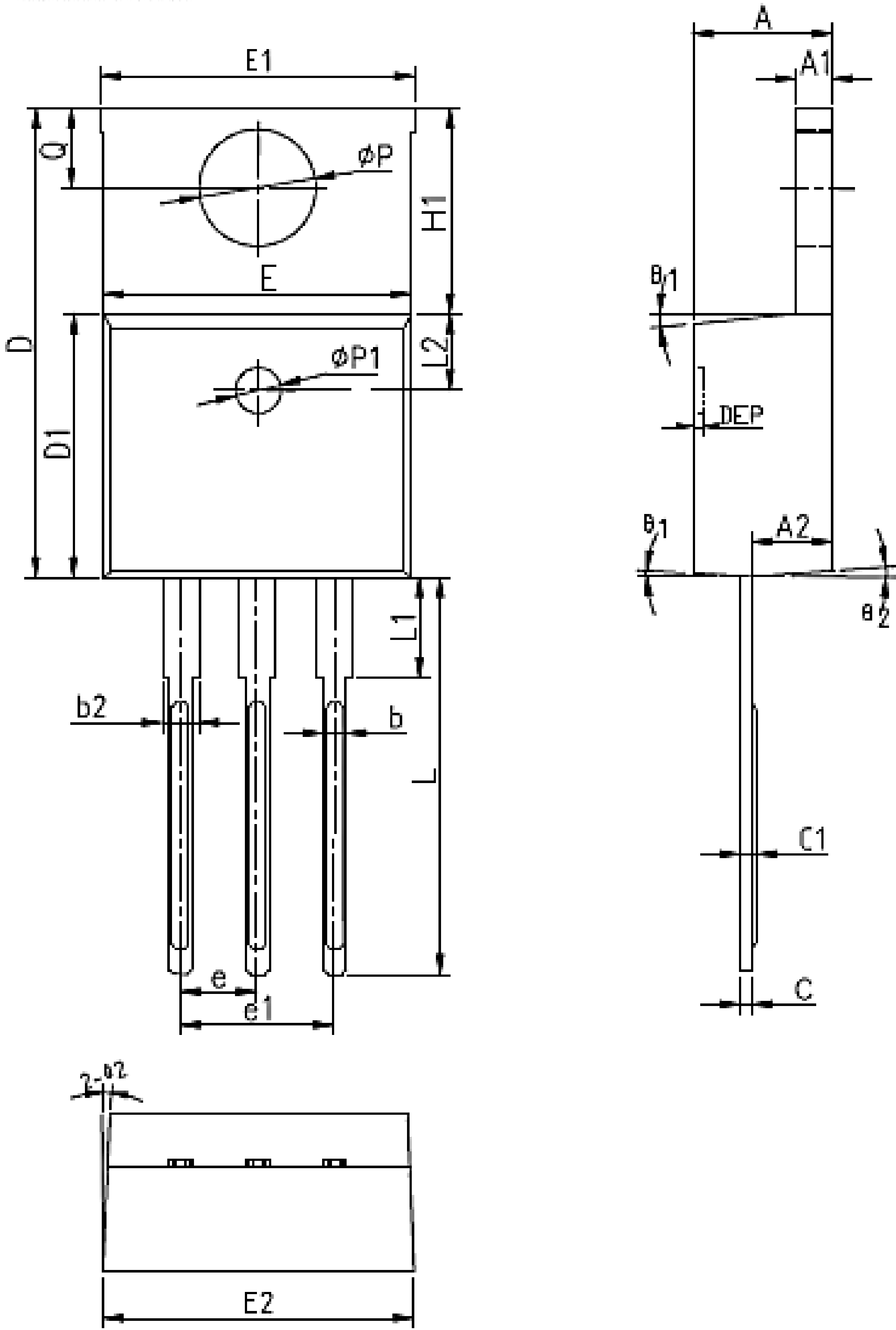


Maximum Rated Forward Biased Safe Operating Area



Transient Thermal Response, Junction-to-Ambient





E1
ØP
Q
H1
E
D
ØP1
L2
D1
L1
b2
b
L
e
e1
E2
A
A1
θ1
DEP
A2
θ2
C1
C

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COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	3.556	4.191	4.826	0.140	0.165	0.190
A1	0.508	1.397	1.40	0.020	0.055	0.055
A2	2.032	2.476	2.921	0.080	0.097	0.115
b	0.356	0.633	0.91	0.014	0.025	0.036
b2	1.05	1.21	1.37	0.041	0.048	0.054
c	0.31	0.46	0.61	0.012	0.018	0.024
c1	0.33	0.465	0.60	0.013	0.018	0.024
D	14.224	15.367	16.51	0.560	0.605	0.650
D1	8.382	8.816	9.25	0.330	0.347	0.364
E	9.652	10.16	10.668	0.380	0.400	0.420
E1	10.10	10.25	10.35	0.398	0.404	0.407
E2	10.00	10.10	10.20	0.394	0.398	0.402
e	2.54 BSC			0.100 BSC		
e1	5.08 BSC			0.200 BSC		
H1	5.842	6.35	6.858	0.230	0.250	0.270
L	12.70	13.716	14.732	0.500	0.540	0.580
L1	3.56	5.145	6.35	0.140	0.203	0.250
L2	2.50 REF			0.098 REF		
ΦP	3.55	3.72	3.89	0.140	0.146	0.153
Q	2.54	2.997	3.048	0.102	0.108	0.114
θ1	5°	7°	9°	5°	7°	9°
θ2	1°	3°	5°	1°	3°	5°
ΦP1	1.40	1.75	2.10	0.055	0.069	0.083
DEP	0.05	0.10	0.20	0.002	0.004	0.008

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ICEMOS SUPERJUNCTION PATENT PORTFOLIO

ICEMOS GRANTED PATENTS

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US7,446,018
US7,579,607
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US7,795,045
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US7,944,018
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US8,030,133

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US7,227,197B2
US7,304,944B2
US7,052,982B2
US7,339,252
US7,410,891
US7,439,583
US7,227,197B2
US6,635,906
US6,936,867
US7,015,104
US9,109,110
US7,271,067
US7,354,818
US7,052,982,
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Note: additional patents in China, Korea, Japan, Taiwan, Europe have also been granted to IceMOS and 3D Semi for Superjunction MOSFETs with 70 additional Patent applications in process in the USA and the above listed countries.

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Marking Information

YY = Last two digits of the year

WW = Work week calendar on Icemos subcon assembly & test house

***** = Initial for Icemos subcon assembly and test house

XXXXXX = Lot ID

ICE4N73 = ICE is Icemos logo and 4N73 is a designated device part number